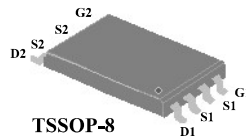


N-Channel Power MOSFET

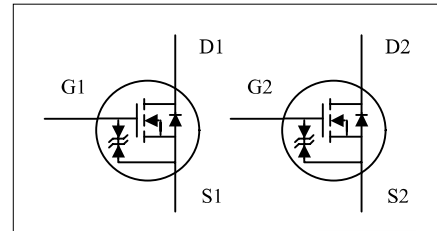
- ▼ Low on-resistance
- ▼ Capable of 1.8V Gate Drive
- ▼ Optimal DC/DC Battery Application
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	20V
$R_{DS(ON)}$	11m Ω
I_D	8A

Description

Advanced Power MOSFETs from AP provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Drain Current ³ , V_{GS} @ 4.5V	8	A
$I_D@T_A=70^\circ C$	Drain Current ³ , V_{GS} @ 4.5V	5.1	A
I_{DM}	Pulsed Drain Current ¹	30	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	1	W
	Linear Derating Factor	0.01	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	125	$^\circ C/W$

N-Channel Power MOSFET
Electrical Characteristics@T_j=25 C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =6A	-	-	14	mΩ
		V _{GS} =2.5V, I _D =4A	-	-	18	mΩ
		V _{GS} =1.8V, I _D =3A	-	-	30	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.3	-	1	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =6A	-	6	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =16V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±8V, V _{DS} =0V	-	-	+30	uA
Q _g	Total Gate Charge ²	I _D =6A	-	28	45	nC
Q _{gs}	Gate-Source Charge	V _{DS} =16V	-	4	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	9	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	11	-	ns
t _r	Rise Time	I _D =1A	-	14	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	22	-	ns
t _f	Fall Time	V _{GS} =5V	-	58	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1630	2600	pF
C _{oss}	Output Capacitance	V _{DS} =20V	-	295	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	270	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.8	2.7	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =0.84A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ²	I _S =6A, V _{GS} =0V,	-	30	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	30	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board ; 208°C/W when mounted on Min. copper pad.

N-Channel Power MOSFET

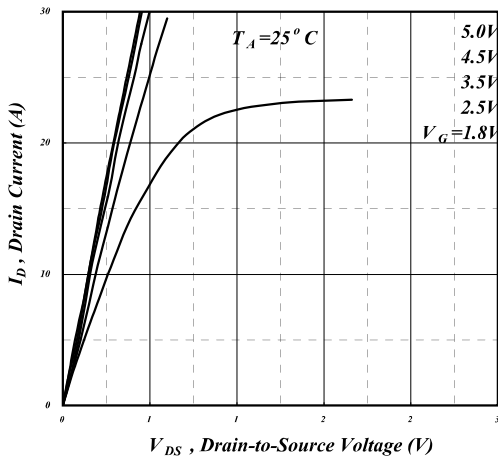


Fig 1. Typical Output Characteristics

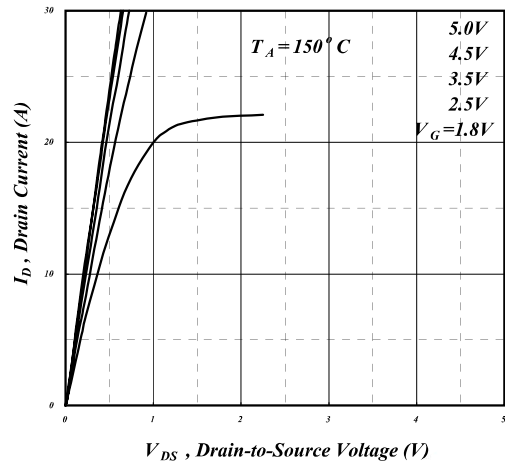


Fig 2. Typical Output Characteristics

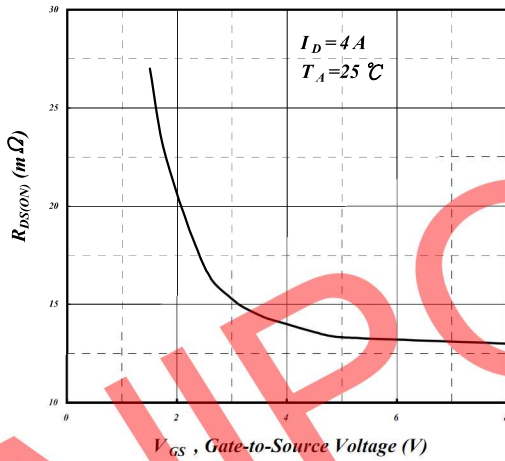


Fig 3. On-Resistance v.s. Gate Voltage

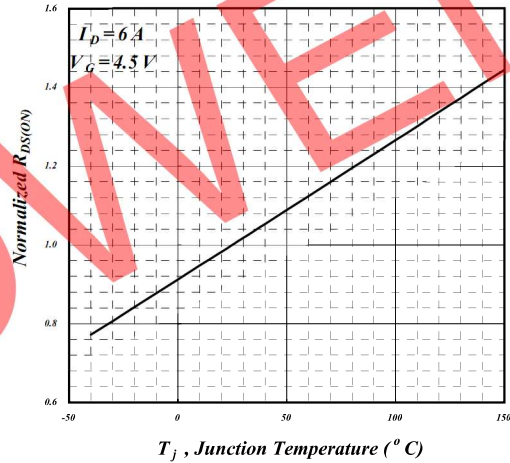


Fig 4. Normalized On-Resistance v.s. Junction Temperature

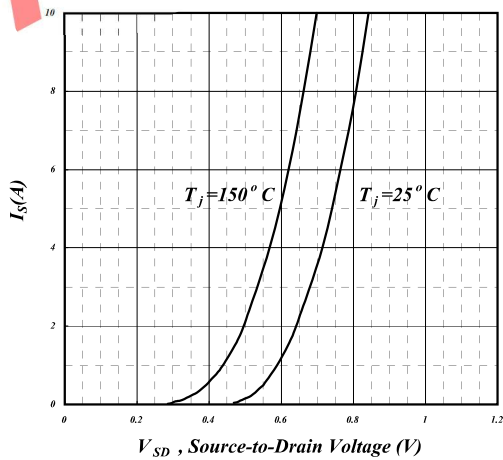


Fig 5. Forward Characteristic of Reverse Diode

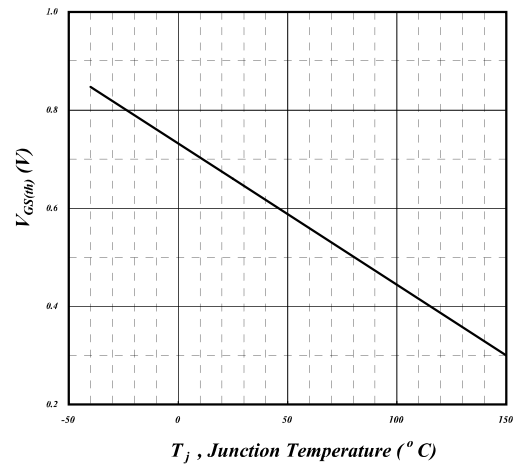


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

N-Channel Power MOSFET

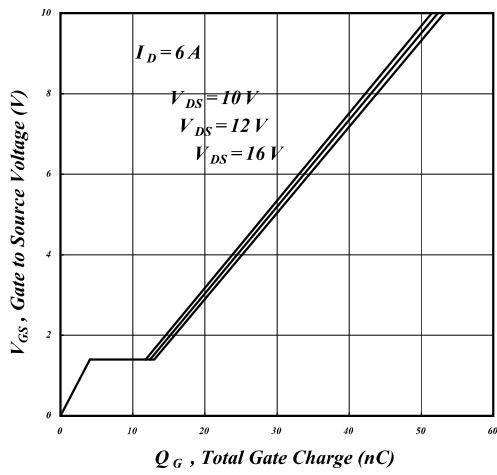


Fig 7. Gate Charge Characteristics

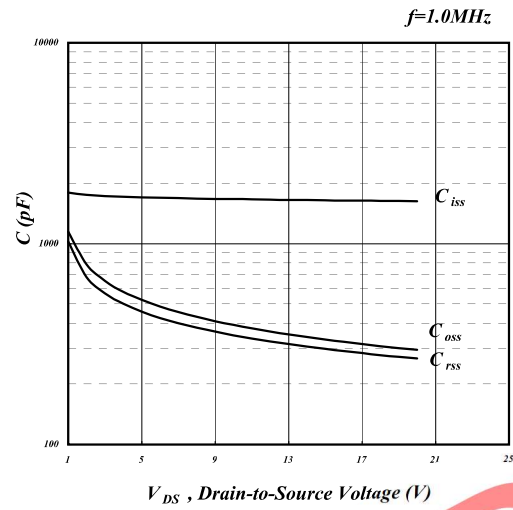


Fig 8. Typical Capacitance Characteristics

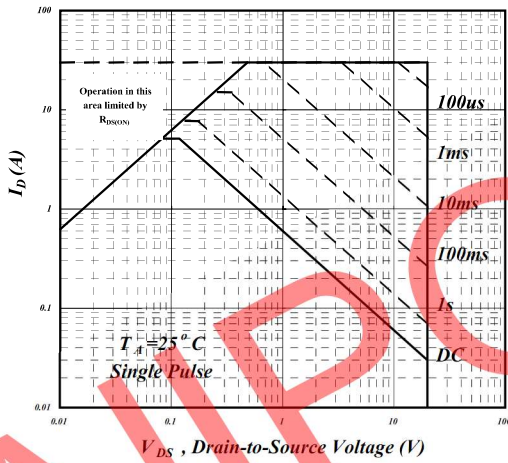


Fig 9. Maximum Safe Operating Area

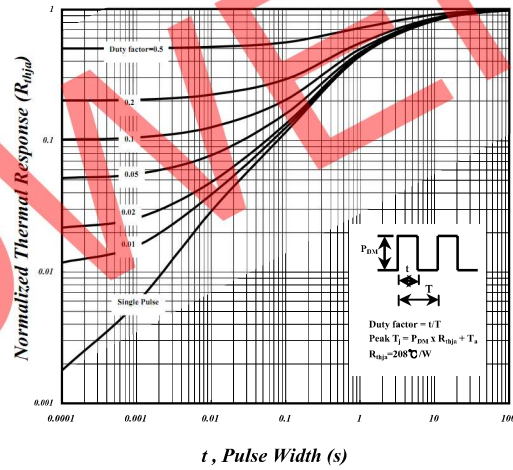


Fig 10. Effective Transient Thermal Impedance

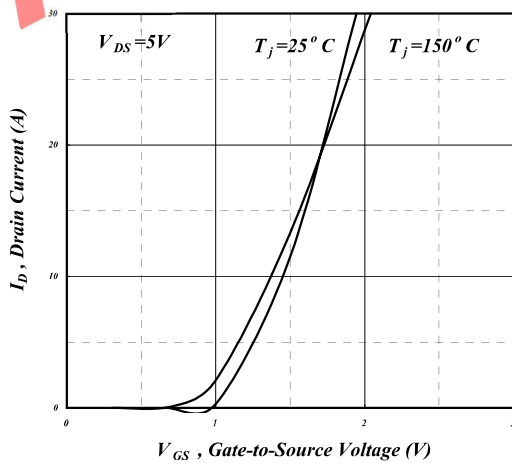


Fig 11. Transfer Characteristics

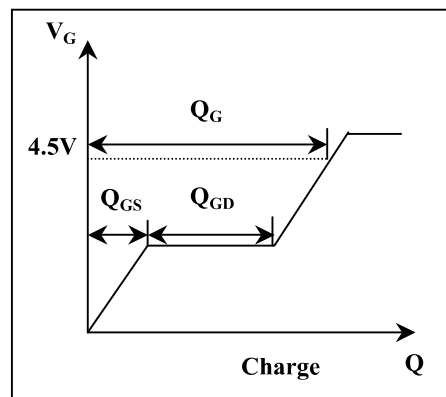
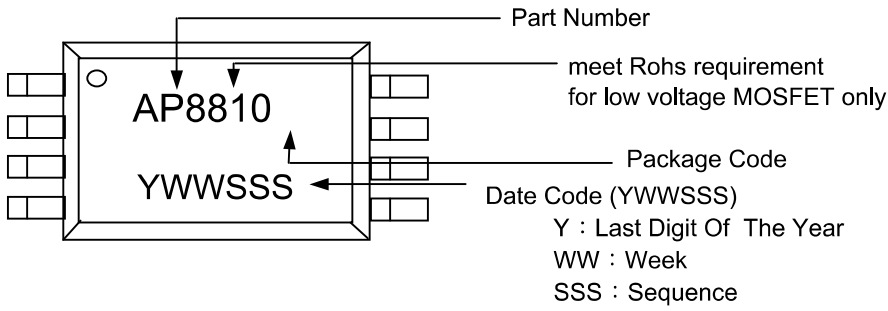


Fig 12. Gate Charge Waveform

MARKING INFORMATION



AIIPOWER